

N-channel 800 V, 2.8 Ω typ., 2.5 A Zener-protected SuperMESH™ 5 Power MOSFET in DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet – production data

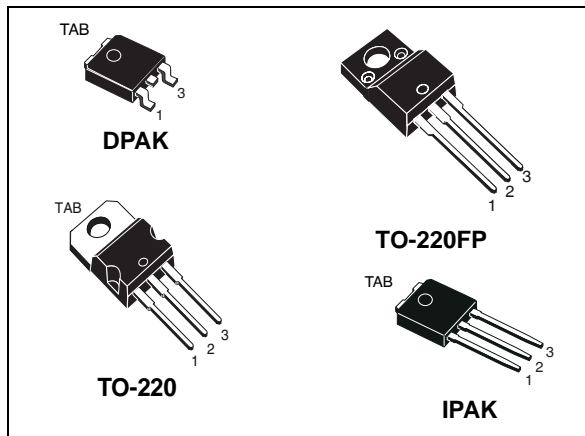
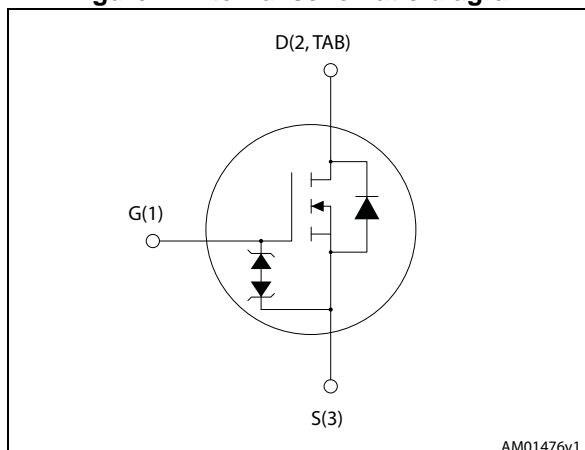


Figure 1. Internal schematic diagram



Features

| Order codes | V_{DS} | $R_{DS(on)max}$ | I_D | P_{TOT} |
|-------------|----------|-----------------|-------|-----------|
| STD3N80K5 | 800 V | 3.5 Ω | 2.5 A | 60 W |
| STF3N80K5 | | | | 20 W |
| STP3N80K5 | | | | 60 W |
| STU3N80K5 | | | | |

- TO-220 worldwide best $R_{DS(on)}$
- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using SuperMESH™ 5 technology. This revolutionary, avalanche-rugged, high voltage Power MOSFET technology is based on an innovative proprietary vertical structure. The result is a drastic reduction in on-resistance and ultra low gate charge for applications which require superior power density and high efficiency.

Table 1. Device summary

| Order code | Marking | Package | Packaging |
|------------|---------|----------|---------------|
| STD3N80K5 | 3N80K5 | DPAK | Tape and reel |
| STF3N80K5 | | TO-220FP | Tube |
| STP3N80K5 | | TO-220 | |
| STU3N80K5 | | IPAK | |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | | | | Unit |
|--------------------|--|--------------------|----------|--------|------|------|
| | | DPAK | TO-220FP | TO-220 | IPAK | |
| V_{GS} | Gate- source voltage | 30 | | | | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ °C}$ | 2.5 ⁽¹⁾ | | | | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ °C}$ | 1.6 | | | | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 10 | | | | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ °C}$ | 60 | 20 | 60 | 60 | W |
| I_{AR} | Max current during repetitive or single pulse avalanche (pulse width limited by T_{jmax}) | 1 | | | | A |
| E_{AS} | Single pulse avalanche energy (starting $T_J = 25\text{ °C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$) | 65 | | | | mJ |
| $dv/dt^{(3)}$ | Peak diode recovery voltage slope | 4.5 | | | | V/ns |
| $dv/dt^{(4)}$ | MOSFET dv/dt ruggedness | 50 | | | | V/ns |
| T_j T_{stg} | Operating junction temperature Storage temperature | -55 to 150 | | | | °C |

1. For TO-220FP limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 2.5\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, peak $V_{DS} \leq V_{(BR)DSS}$
4. $V_{DS} \leq 640\text{ V}$

Table 3. Thermal data

| Symbol | Parameter | Value | | | | Unit |
|----------------|----------------------------------|-------------------|----------|--------|------|------|
| | | DPAK | TO-220FP | TO-220 | IPAK | |
| $R_{thj-case}$ | Thermal resistance junction-case | 2.08 | 6.25 | 2.08 | | °C/W |
| $R_{thj-pcb}$ | Thermal resistance junction-pcb | 50 ⁽¹⁾ | | | | |
| $R_{thj-amb}$ | Thermal resistance junction-amb | | 62.5 | 62.5 | 100 | |

1. When mounted on FR-4 board of 1 inch², 2 oz Cu

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|----------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage ($V_{GS} = 0$) | $I_D = 1\text{ mA}$ | 800 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = 800\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 800\text{ V}$, $T_J = 125\text{ °C}$ | | | 50 | μA |
| I_{GSS} | Gate body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20\text{ V}$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$ | 3 | 4 | 5 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}$, $I_D = 1\text{ A}$ | | 2.8 | 3.5 | Ω |

Table 5. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------|---------------------------------------|--|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$ | - | 130 | - | pF |
| C_{oss} | Output capacitance | | - | 14 | - | pF |
| C_{rss} | Reverse transfer capacitance | | - | 0.6 | - | pF |
| $C_{o(tr)}^{(1)}$ | Equivalent capacitance time related | $V_{GS} = 0$, $V_{DS} = 0$ | - | 20 | - | pF |
| $C_{o(er)}^{(2)}$ | Equivalent capacitance energy related | | - | 9 | - | pF |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz}$, $I_D = 0$ | - | 15.5 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 640\text{ V}$, $I_D = 2.5\text{ A}$ $V_{GS} = 10\text{ V}$ | - | 9.5 | - | nC |
| Q_{gs} | Gate-source charge | | - | 1.5 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 7.5 | - | nC |

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 400\text{ V}$, $I_D = 1.25\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ | - | 8.5 | - | ns |
| t_r | Rise time | | - | 7.5 | - | ns |
| $t_{d(off)}$ | Turn-off delay time | | - | 20.5 | - | ns |
| t_f | Fall time | | - | 25 | - | ns |

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain current | | - | | 2.5 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 10 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 2.5\text{ A}$, $V_{GS} = 0$ | - | | 1.5 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 2.5\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, | - | 265 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 1.2 | | μC |
| I_{RRM} | Reverse recovery current | | - | 9.2 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 2.5\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$ | - | 430 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 1.9 | | μC |
| I_{RRM} | Reverse recovery current | | - | 8.8 | | A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-------------------------------|--|------|------|------|------|
| $V_{(BR)GSO}$ | Gate-source breakdown voltage | $I_{GS} = \pm 1\text{ mA}$, $I_D = 0$ | 30 | - | - | V |

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device’s ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAK

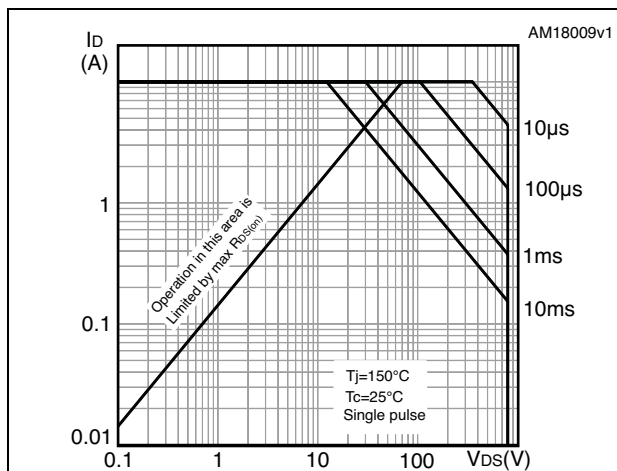


Figure 3. Thermal impedance for DPAK and IPAK

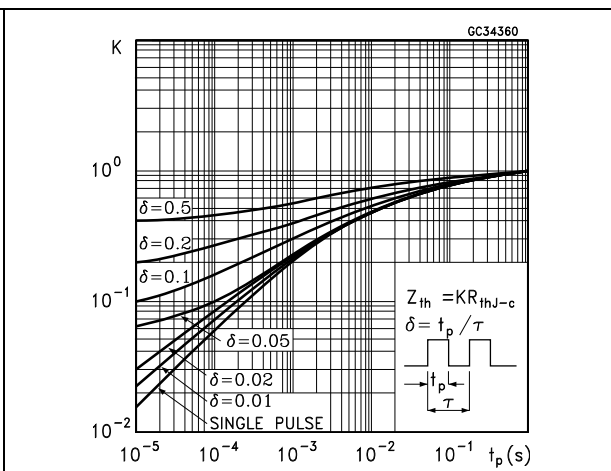


Figure 4. Safe operating area for TO-220FP

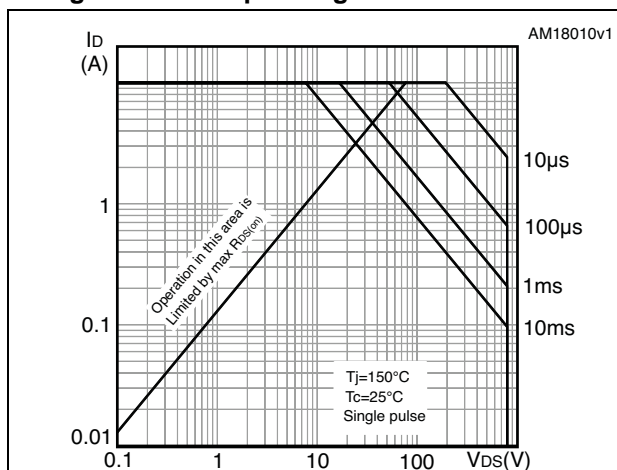


Figure 5. Thermal impedance for TO-220FP

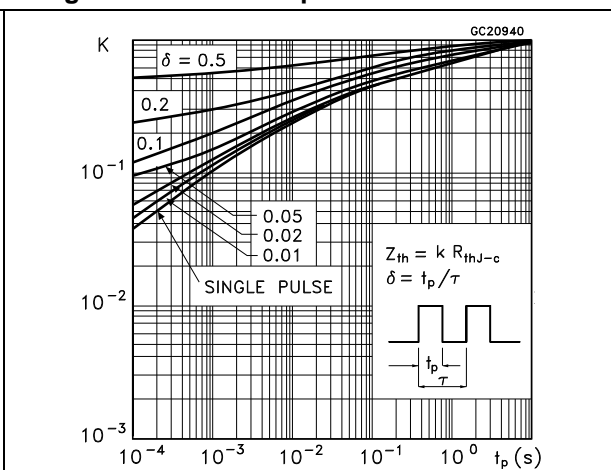


Figure 6. Safe operating area for TO-220

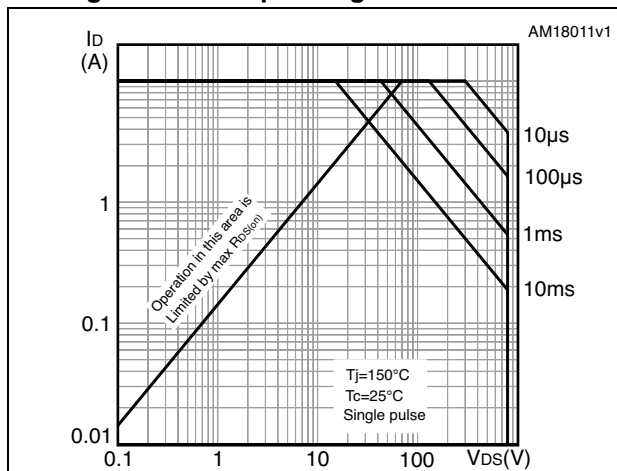


Figure 7. Thermal impedance for TO-220

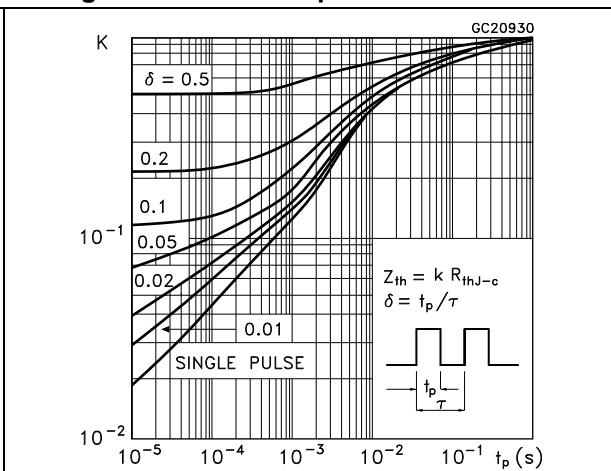


Figure 8. Output characteristics

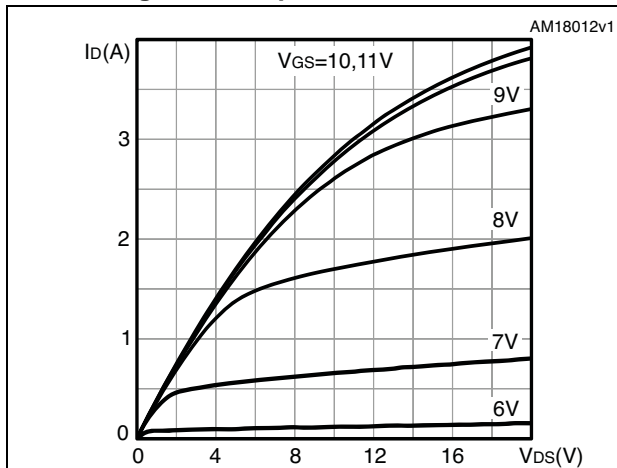


Figure 9. Transfer characteristics

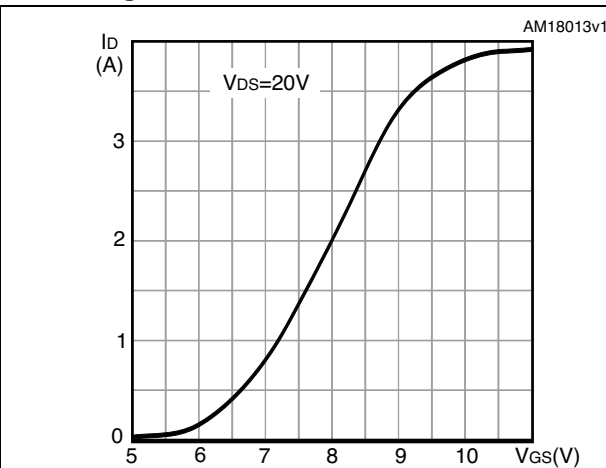


Figure 10. Gate charge vs gate-source voltage

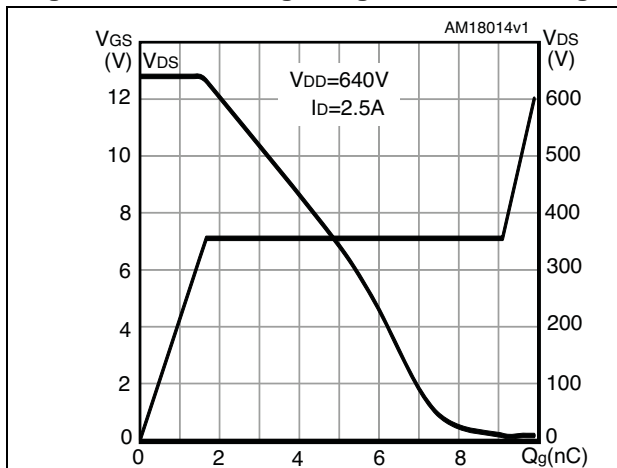


Figure 11. Static drain-source on-resistance

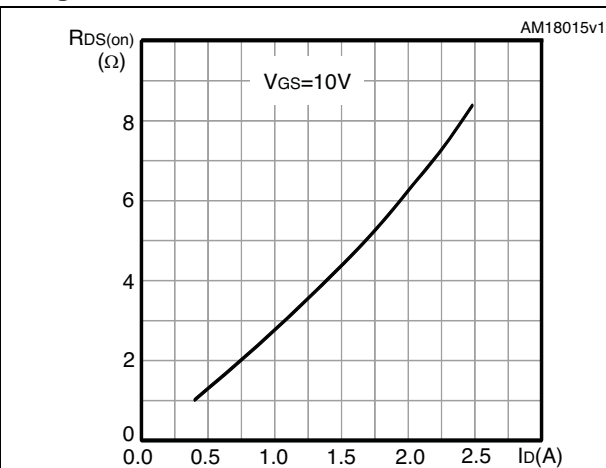


Figure 12. Capacitance variations

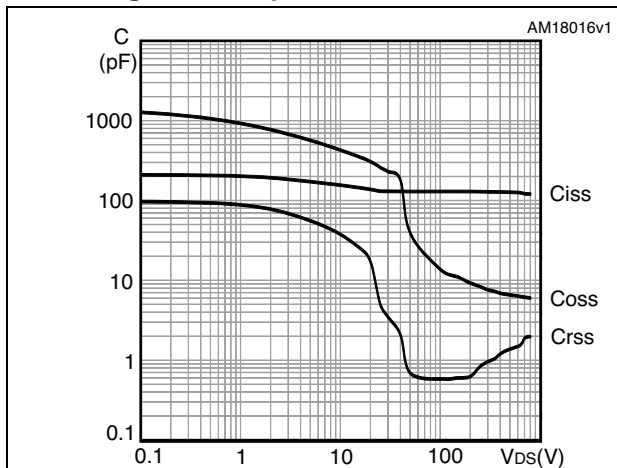


Figure 13. Output capacitance stored energy

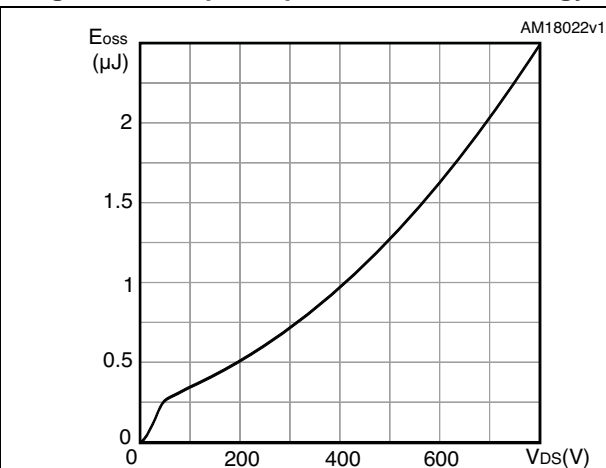


Figure 14. Normalized gate threshold voltage vs temperature

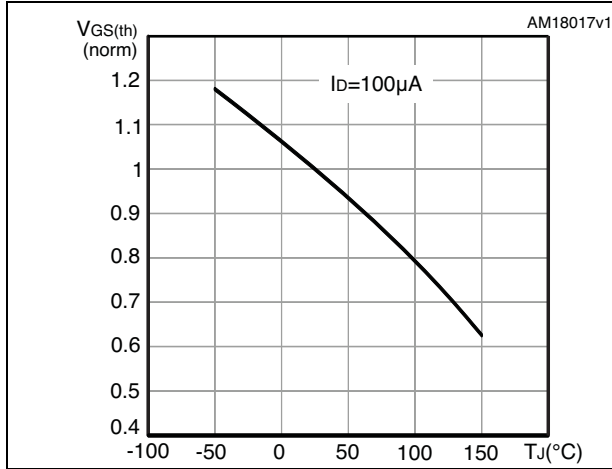


Figure 15. Normalized on-resistance vs temperature

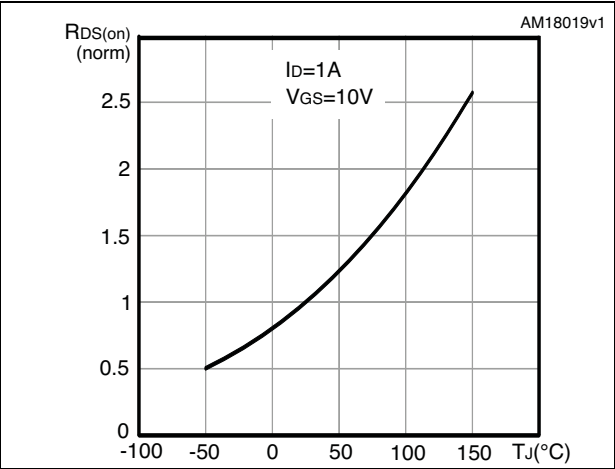


Figure 16. Normalized VDS vs temperature

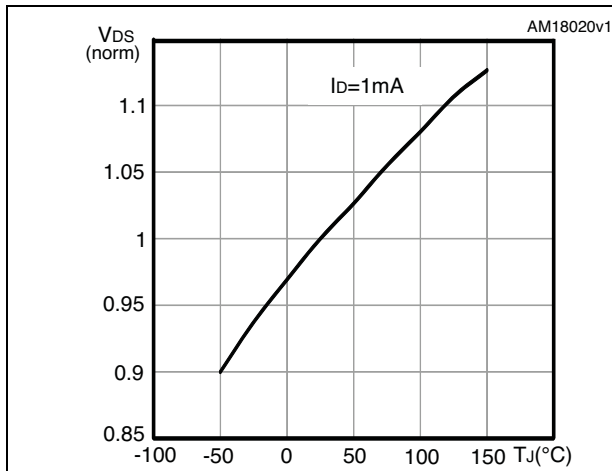
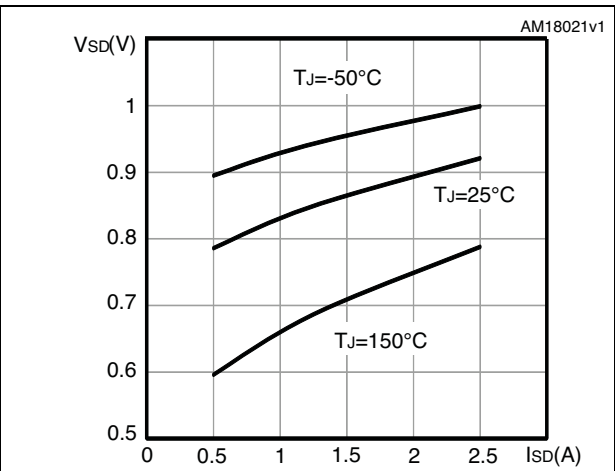


Figure 17. Source-drain diode forward characteristics



3 Test circuits

Figure 18. Switching times test circuit for resistive load



Figure 19. Gate charge test circuit

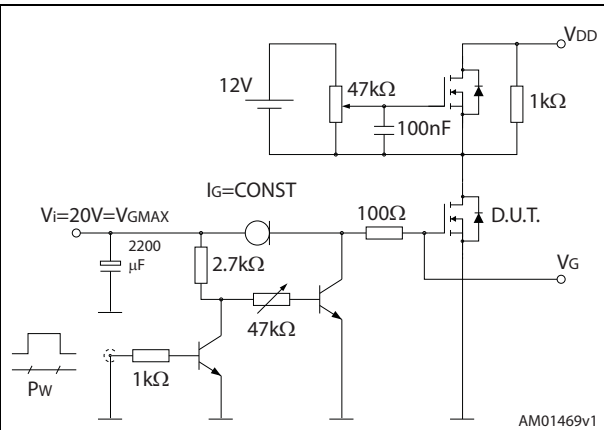


Figure 20. Test circuit for inductive load switching and diode recovery times

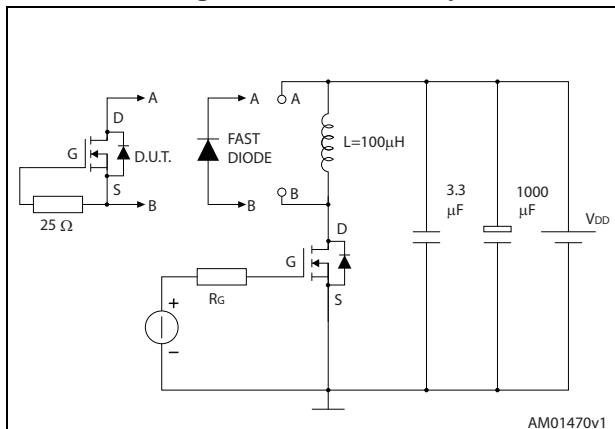


Figure 21. Unclamped inductive load test circuit

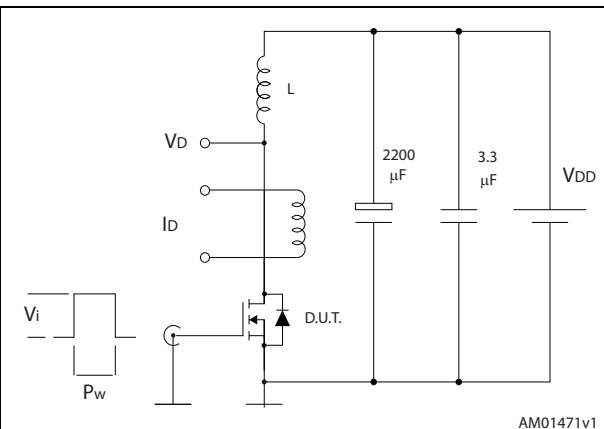


Figure 22. Unclamped inductive waveform

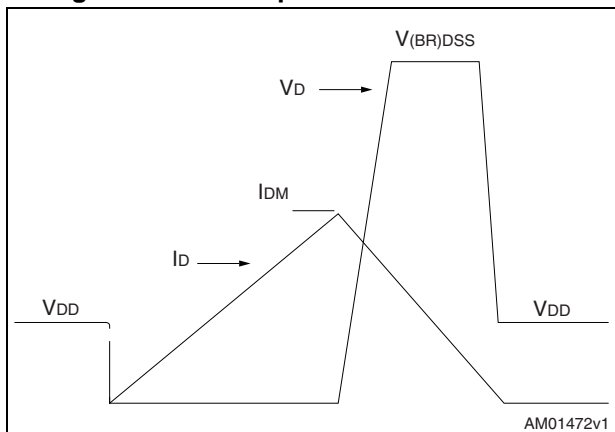
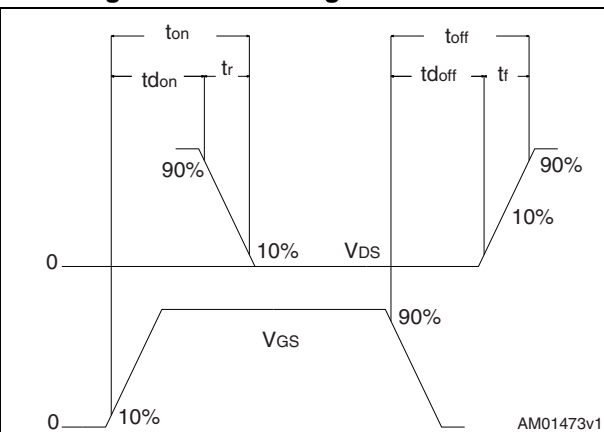


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 24. DPAK (TO-252) type A drawing

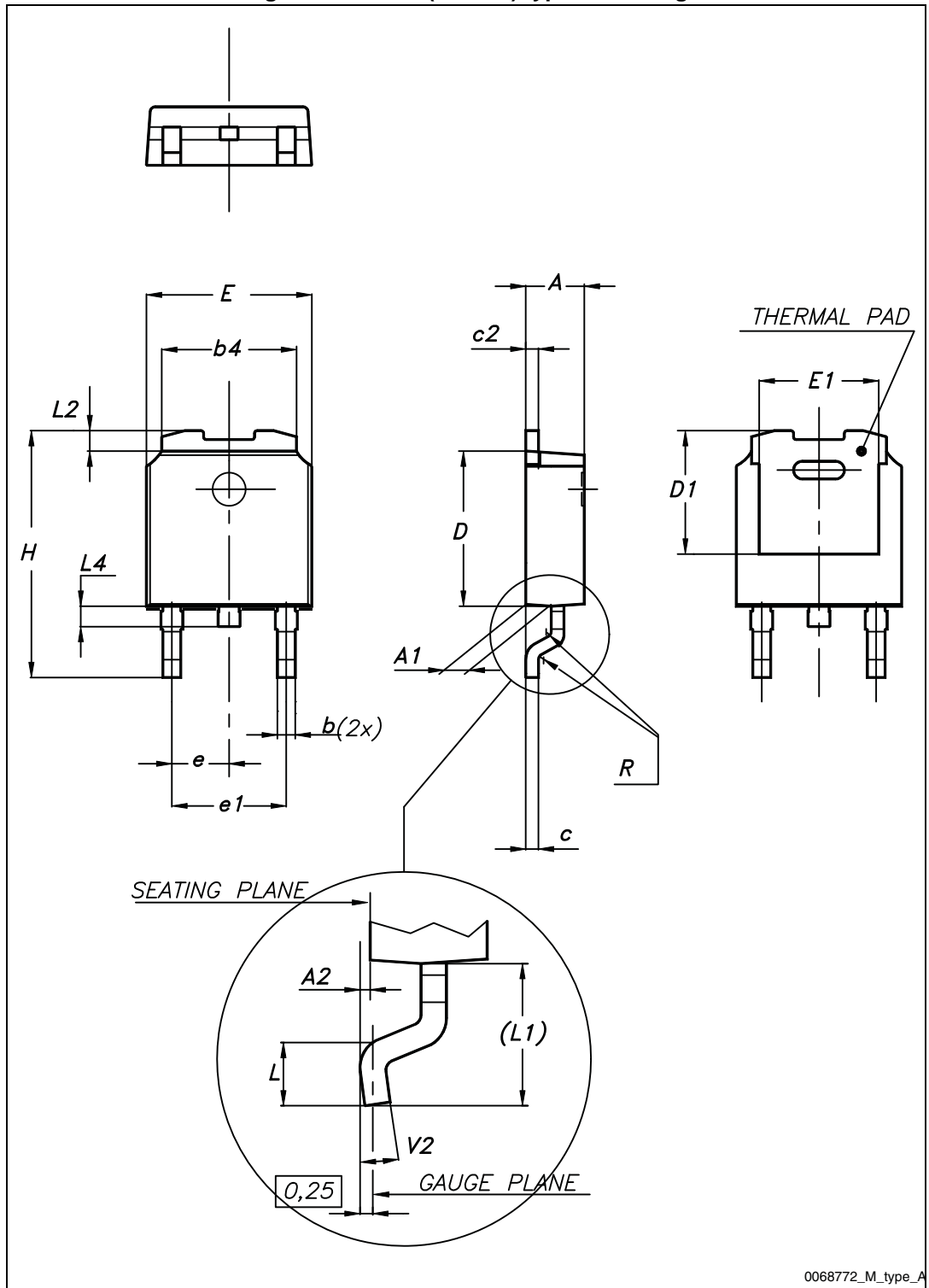
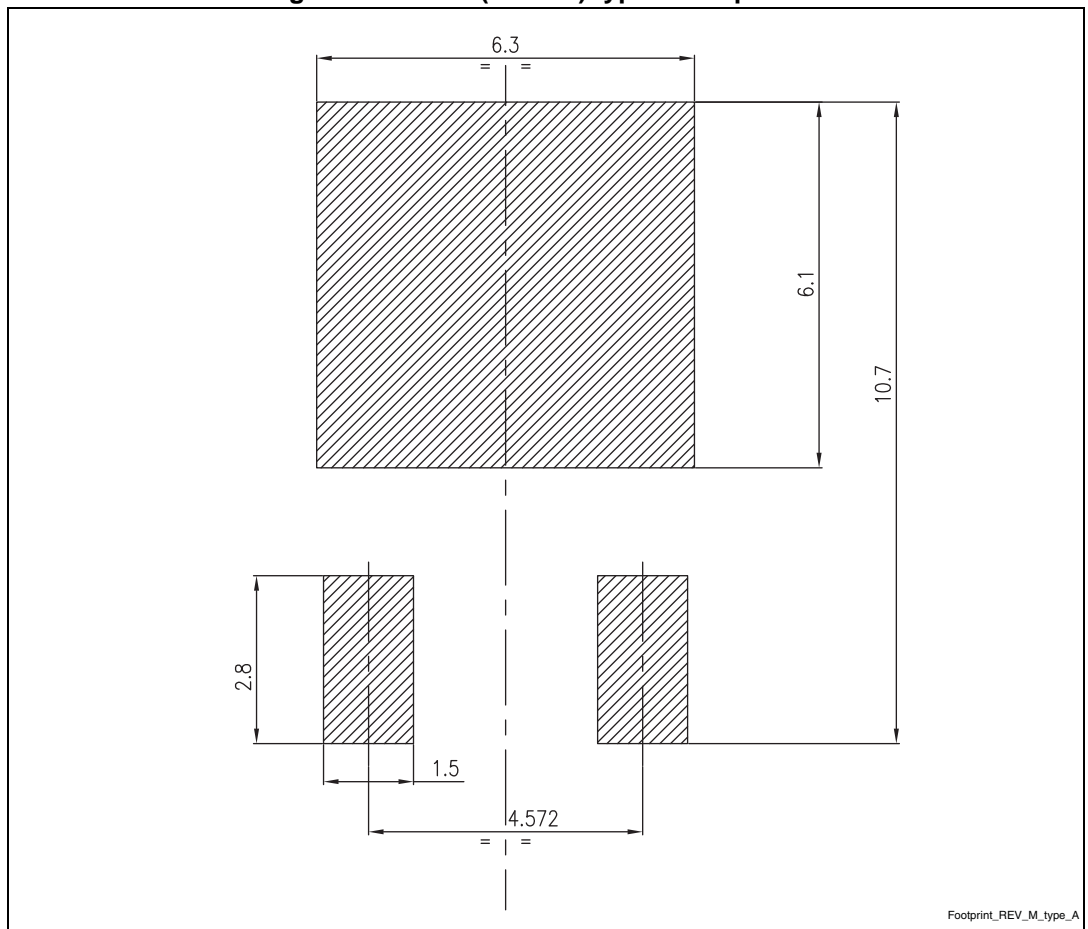


Table 9. DPAK (TO-252) type A mechanical data

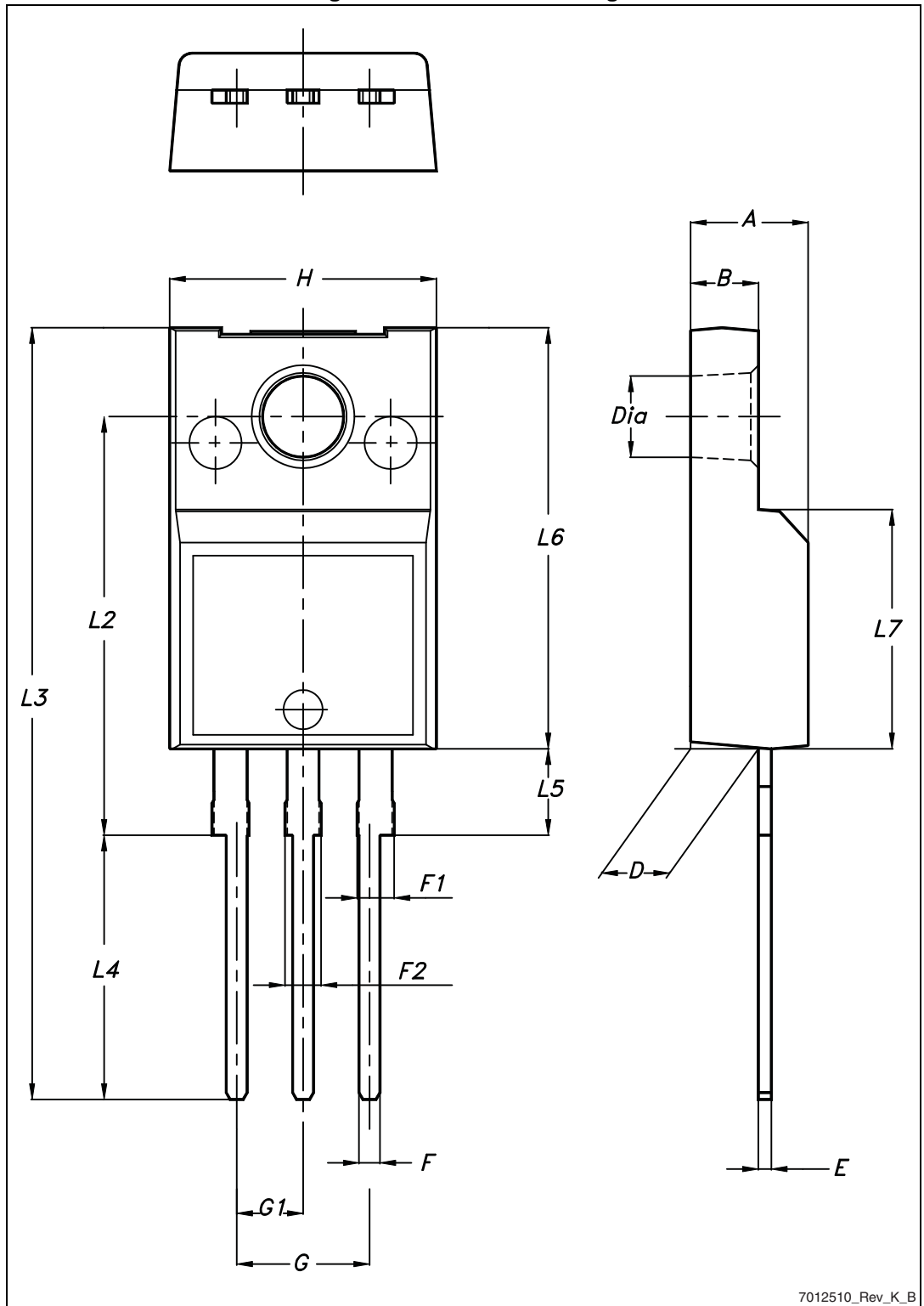
| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | | 5.10 | |
| E | 6.40 | | 6.60 |
| E1 | | 4.70 | |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1.00 | | 1.50 |
| (L1) | | 2.80 | |
| L2 | | 0.80 | |
| L4 | 0.60 | | 1.00 |
| R | | 0.20 | |
| V2 | 0° | | 8° |

Figure 25. DPAK (TO-252) type A footprint (a)



a. All dimensions are in millimeters

Figure 26. TO-220FP drawing



7012510_Rev_K_B

Table 10. TO-220FP mechanical data

| Dim. | mm | | |
|------|------|------|------|
| | Min. | Typ. | Max. |
| A | 4.4 | | 4.6 |
| B | 2.5 | | 2.7 |
| D | 2.5 | | 2.75 |
| E | 0.45 | | 0.7 |
| F | 0.75 | | 1 |
| F1 | 1.15 | | 1.70 |
| F2 | 1.15 | | 1.70 |
| G | 4.95 | | 5.2 |
| G1 | 2.4 | | 2.7 |
| H | 10 | | 10.4 |
| L2 | | 16 | |
| L3 | 28.6 | | 30.6 |
| L4 | 9.8 | | 10.6 |
| L5 | 2.9 | | 3.6 |
| L6 | 15.9 | | 16.4 |
| L7 | 9 | | 9.3 |
| ∅ | 3 | | 3.2 |

Figure 27. TO-220 drawing

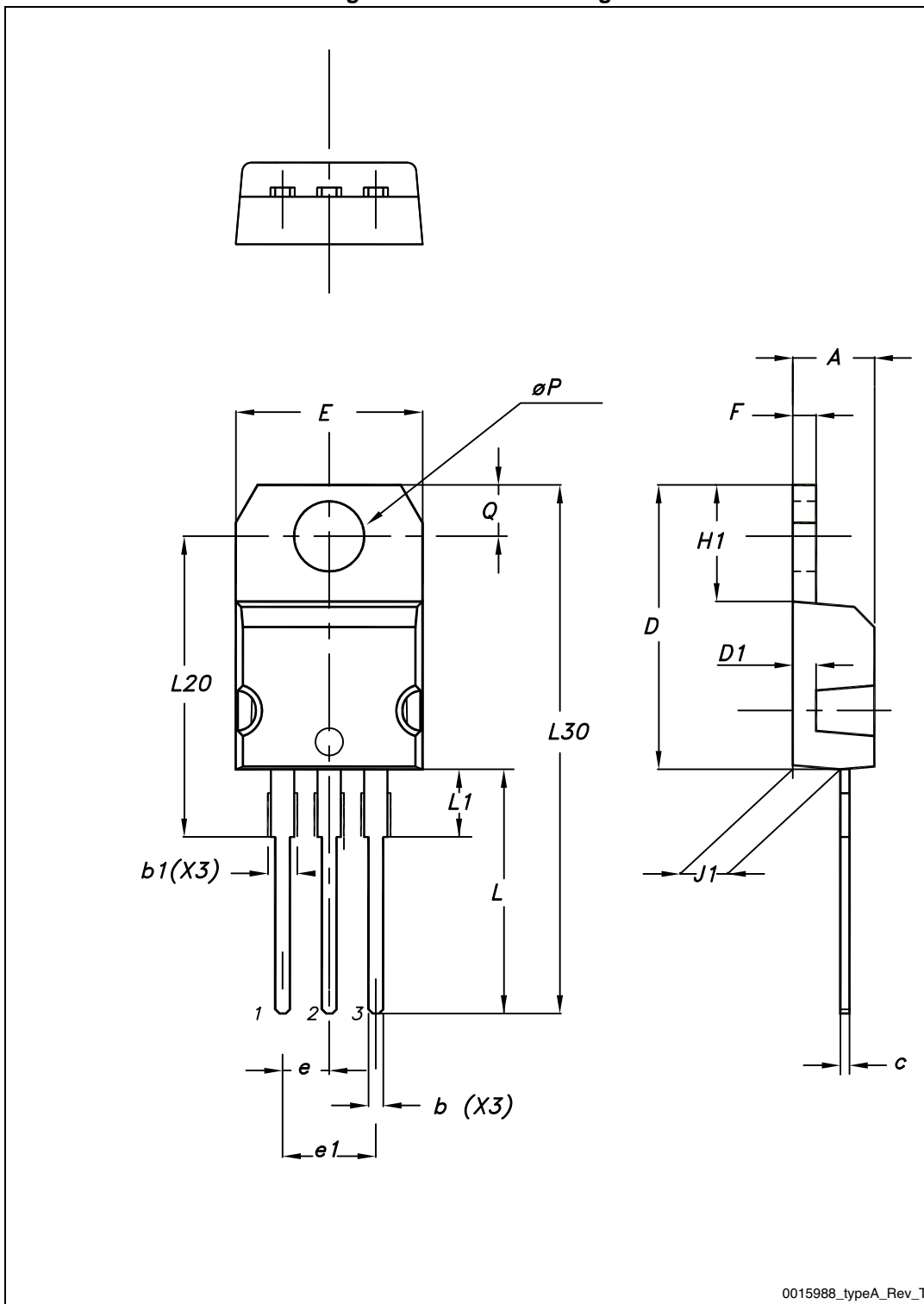
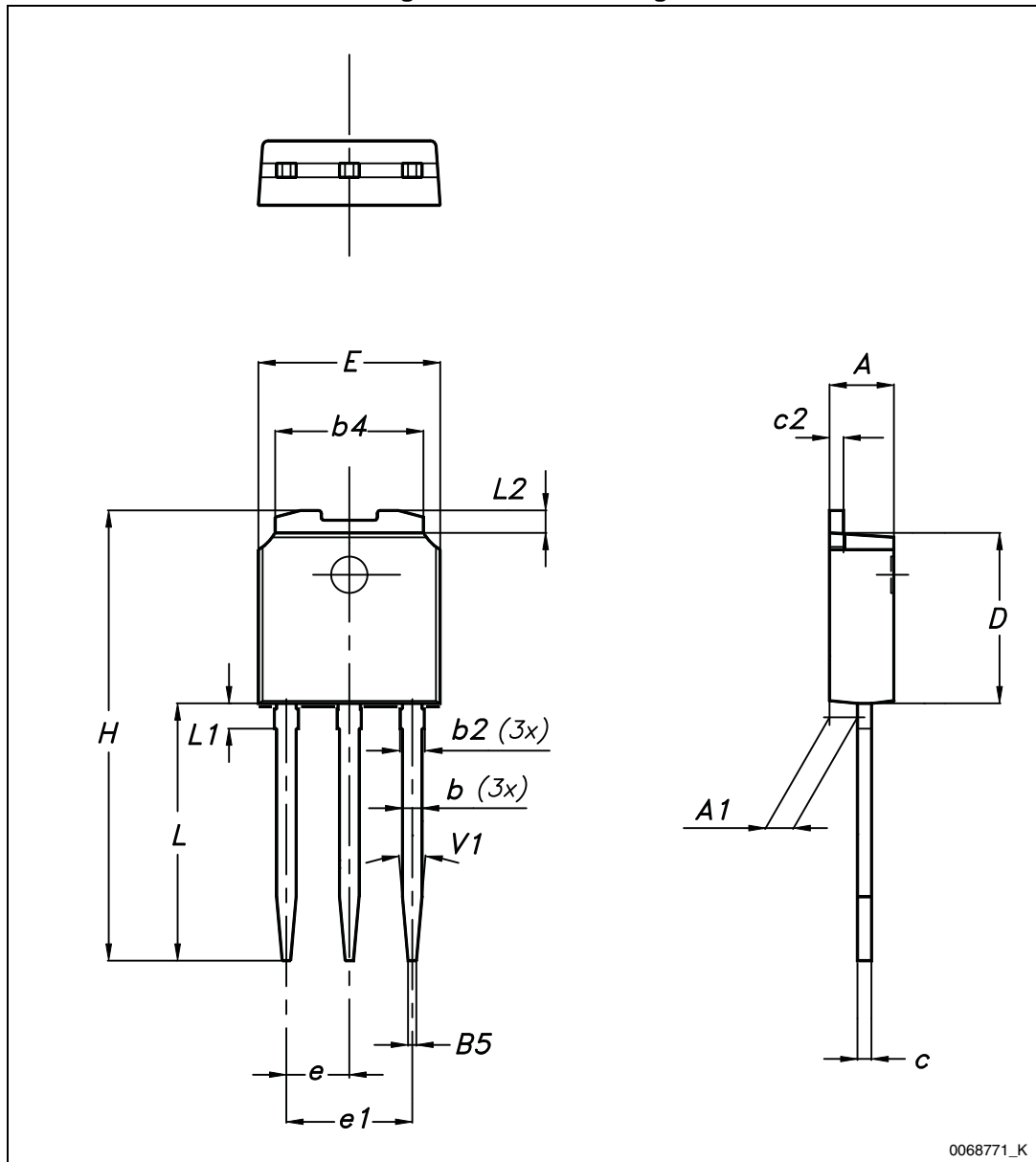


Table 11. TO-220 mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| b | 0.61 | | 0.88 |
| b1 | 1.14 | | 1.70 |
| c | 0.48 | | 0.70 |
| D | 15.25 | | 15.75 |
| D1 | | 1.27 | |
| E | 10 | | 10.40 |
| e | 2.40 | | 2.70 |
| e1 | 4.95 | | 5.15 |
| F | 1.23 | | 1.32 |
| H1 | 6.20 | | 6.60 |
| J1 | 2.40 | | 2.72 |
| L | 13 | | 14 |
| L1 | 3.50 | | 3.93 |
| L20 | | 16.40 | |
| L30 | | 28.90 | |
| ØP | 3.75 | | 3.85 |
| Q | 2.65 | | 2.95 |

Figure 28. IPAK drawing



0068771_K

Table 12. IPAK mechanical data

| DIM | mm. | | |
|-----|------|-------|------|
| | min. | typ. | max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| b | 0.64 | | 0.90 |
| b2 | | | 0.95 |
| b4 | 5.20 | | 5.40 |
| B5 | | 0.30 | |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| E | 6.40 | | 6.60 |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | | 16.10 | |
| L | 9.00 | | 9.40 |
| L1 | 0.80 | | 1.20 |
| L2 | | 0.80 | 1.00 |
| V1 | | 10° | |

5 Packaging information

Figure 29. Tape for DPAK

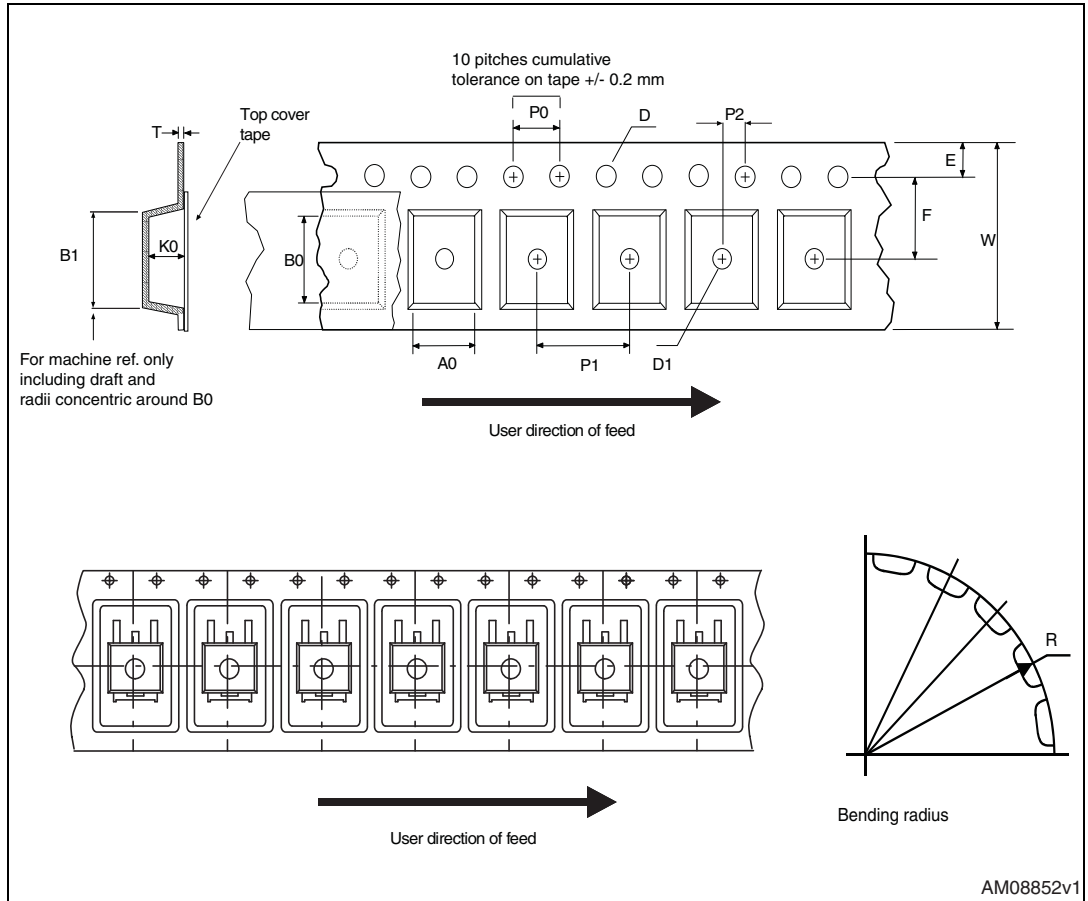


Figure 30. Reel for DPAK

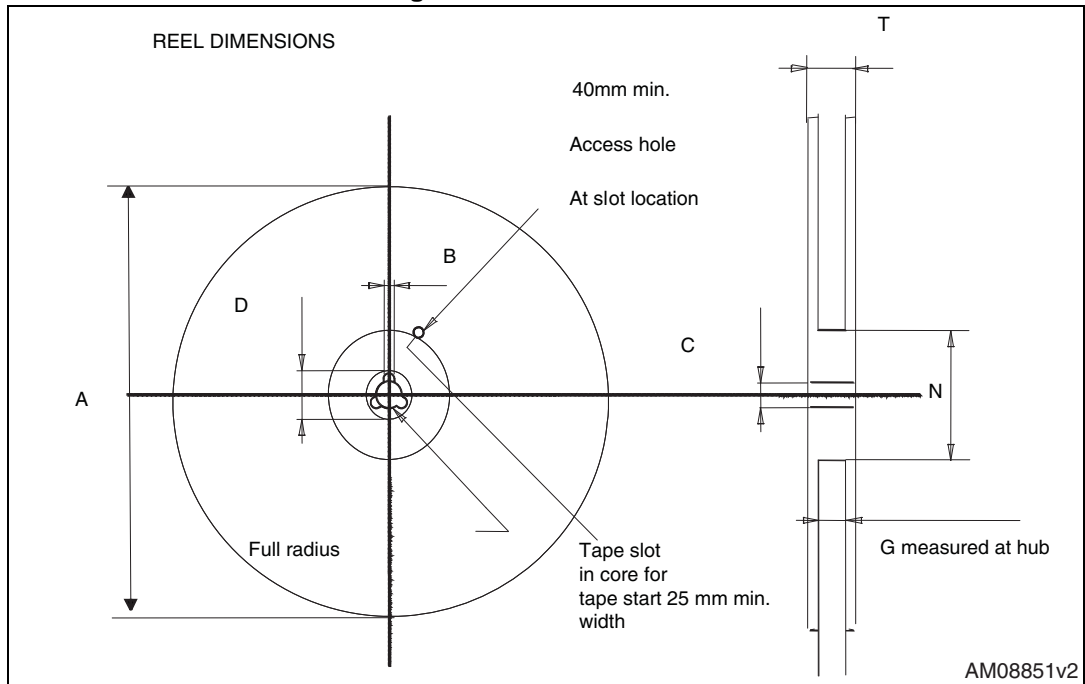


Table 13. DPAK tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|------|-----------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 6.8 | 7 | A | | 330 |
| B0 | 10.4 | 10.6 | B | 1.5 | |
| B1 | | 12.1 | C | 12.8 | 13.2 |
| D | 1.5 | 1.6 | D | 20.2 | |
| D1 | 1.5 | | G | 16.4 | 18.4 |
| E | 1.65 | 1.85 | N | 50 | |
| F | 7.4 | 7.6 | T | | 22.4 |
| K0 | 2.55 | 2.75 | | | |
| P0 | 3.9 | 4.1 | | Base qty. | 2500 |
| P1 | 7.9 | 8.1 | | Bulk qty. | 2500 |
| P2 | 1.9 | 2.1 | | | |
| R | 40 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 15.7 | 16.3 | | | |

6 Revision history

Table 14. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 12-Jul-2013 | 1 | First release. |
| 15-Jan-2014 | 2 | <ul style="list-style-type: none">– Modified: P_{TOT} and E_{AS} values in Table 2– Modified: $R_{thj-case}$ values in Table 3– Modified: the entire typical values in Table 5 and 6– Modified: I_{SD} and I_{SDM} max values and typical values in Table 7– Updated: Table 24 and Table 9– Added: Section 2.1: Electrical characteristics (curves)– Minor text changes |
| 17-Jan-2014 | 3 | <ul style="list-style-type: none">– Modified: Figure 8 and 9– Minor text changes |

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